

Supplementary Materials

Solution Deposition of High-Quality AgBiS₂ Thin-Films via a Binary Diamine-Dithiol Solvent System

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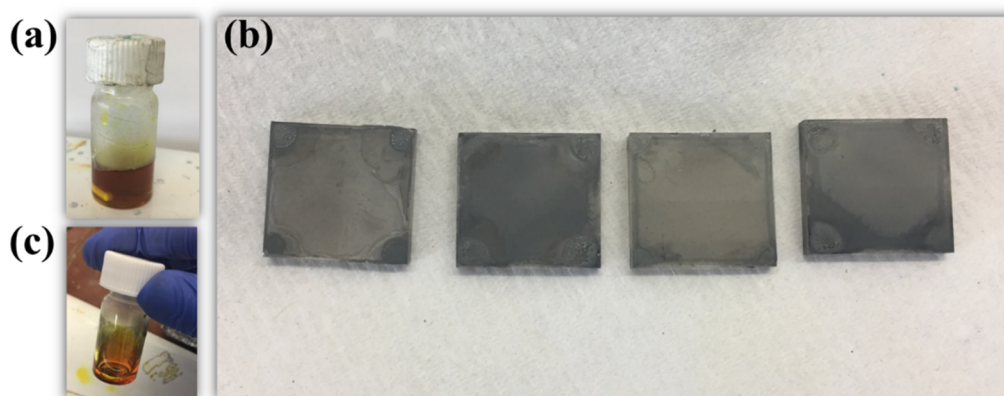


Figure S1. (a) Precursor solution of AgBiS₂ with en: edtH₂ (volume ratio of 10:1) in air. (b) AgBiS₂ thin-films deposited in air at different deposition speed (increasing speed from left to right). (c) Precursor solution of AgBiS₂ in air with a humidity of 65%.

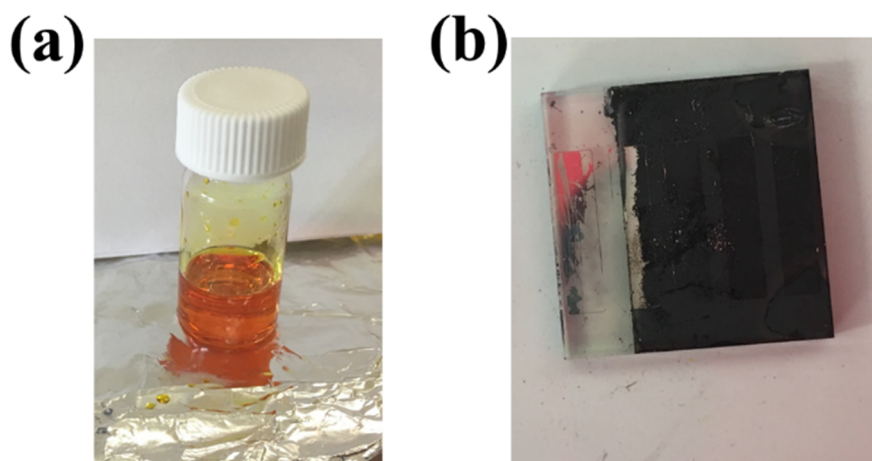


Figure S2. (a) Precursor solution of AgBiS₂ with en: edtH₂ (volume ratio of 10:1), and (b) AgBiS₂ thin-films deposited in N₂ atmosphere.

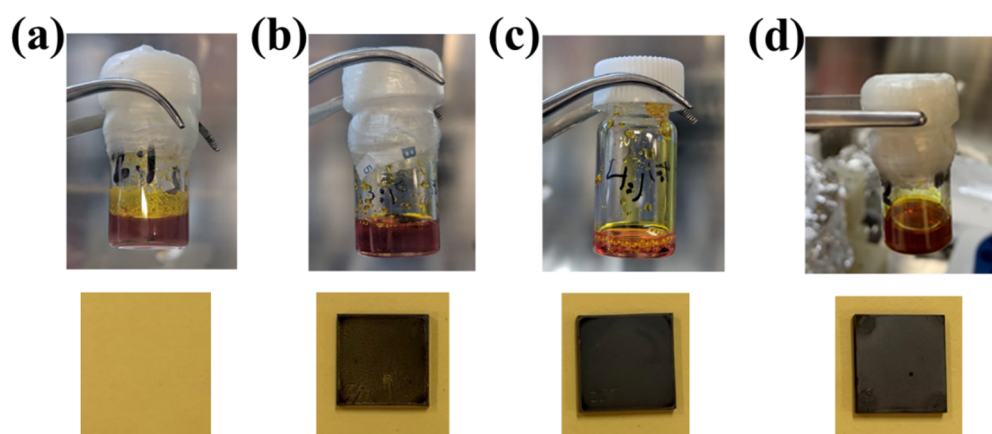


Figure S3. Precursor solution of AgBiS_2 with different en: edtH₂ volume ratio of (a) 2:1, (b) 3:1, (c) 4:1, (d) 5:1, and the corresponding deposited AgBiS_2 thin-films (bottom side).

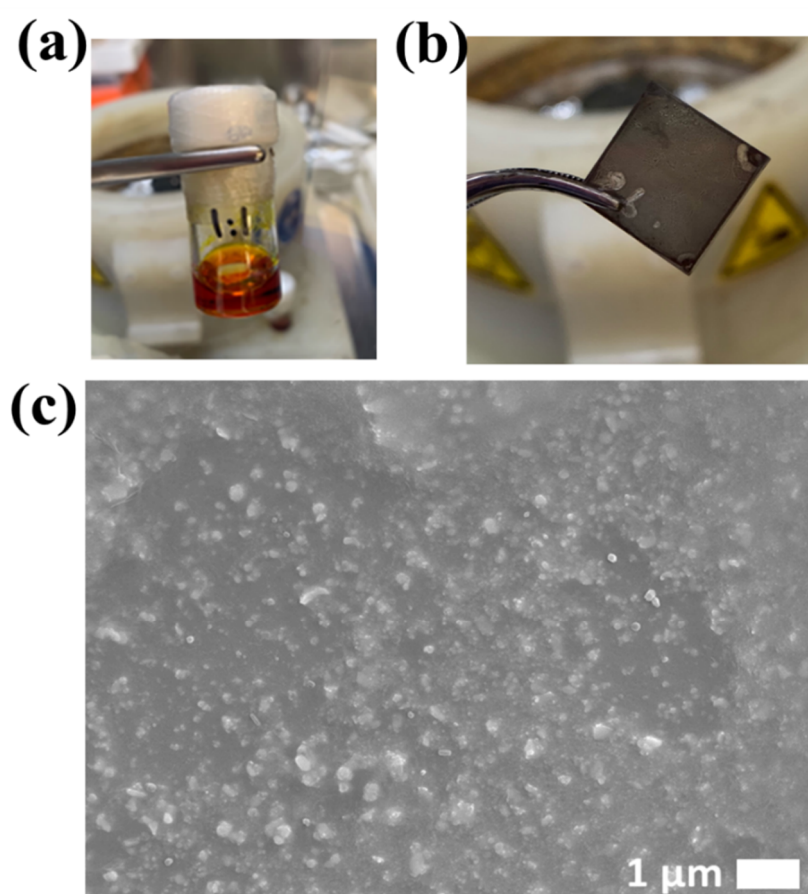


Figure S4. (a) Precursor solution of AgBiS_2 with adding extra sulfur powder, (b) Resultant AgBiS_2 thin-film from the solution with extra sulfur powder, (c) SEM image of the AgBiS_2 thin-film with extra sulfur powder.

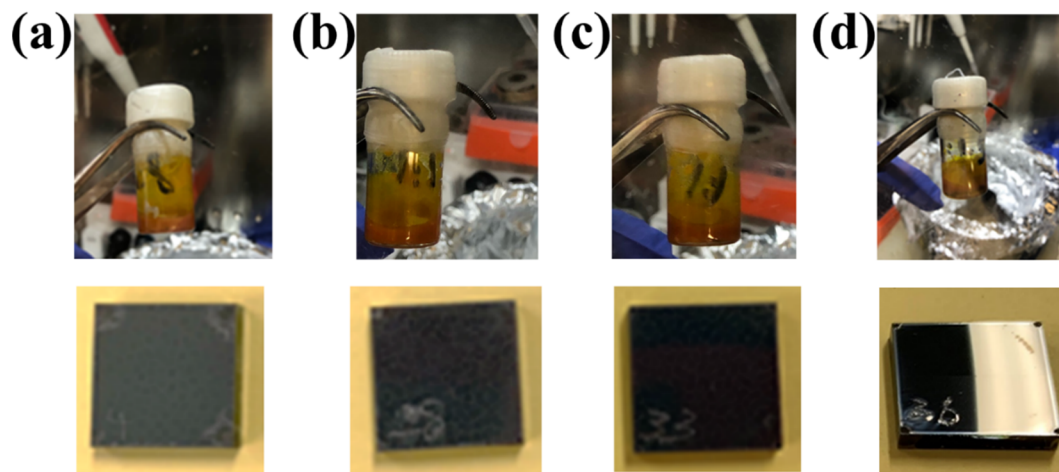


Figure S5. Precursor solutions (upper side) and deposited AgBiS₂ thin-films (downer side) with different Ag₂S: Bi₂S₃ ratios of (a) 1:0.8, (b) 1:1, (c) 1:1.2, (d) 1:1.5.

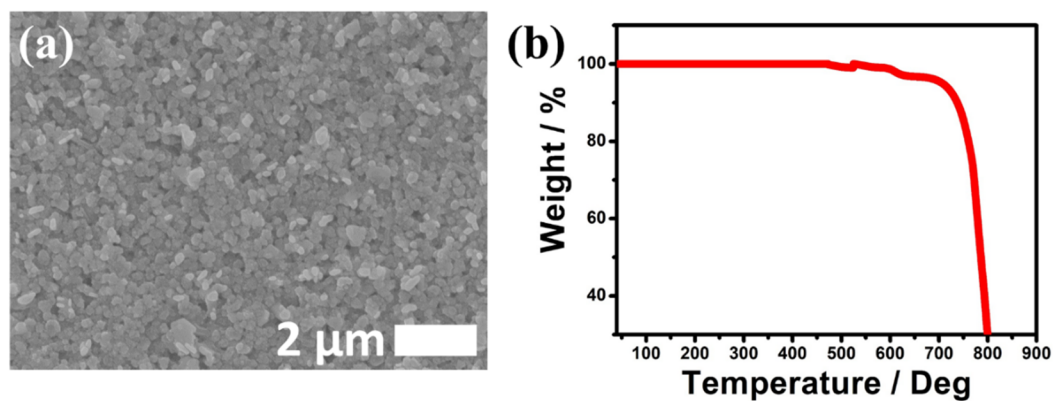


Figure S6. (a) SEM image of AgBiS₂ thin-film with Ag₂S: Bi₂S₃ molar ratio of 1:1.5 annealed at 180 °C. (b) TGA curves of AgBiS₂ in a nitrogen atmosphere.

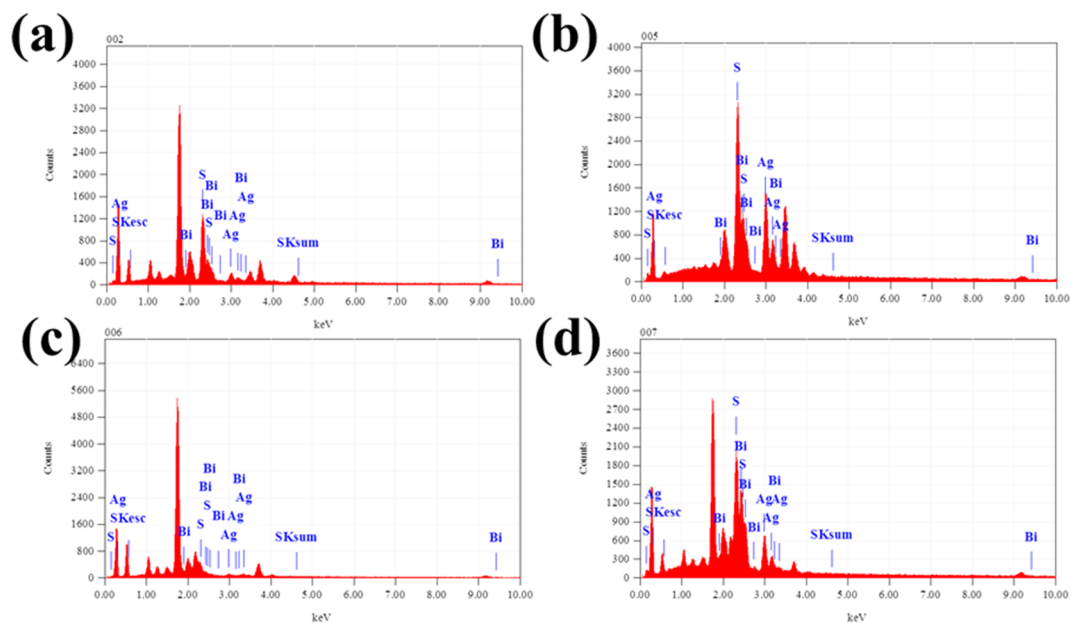


Figure S7. EDS spectrum of the AgBiS₂ thin-films with different Ag₂S: Bi₂S₃ molar ratio of (a) 1:0.8, (b) 1:1, (c) 1:1.2, (d) 1:1.5 annealed at 180 °C.

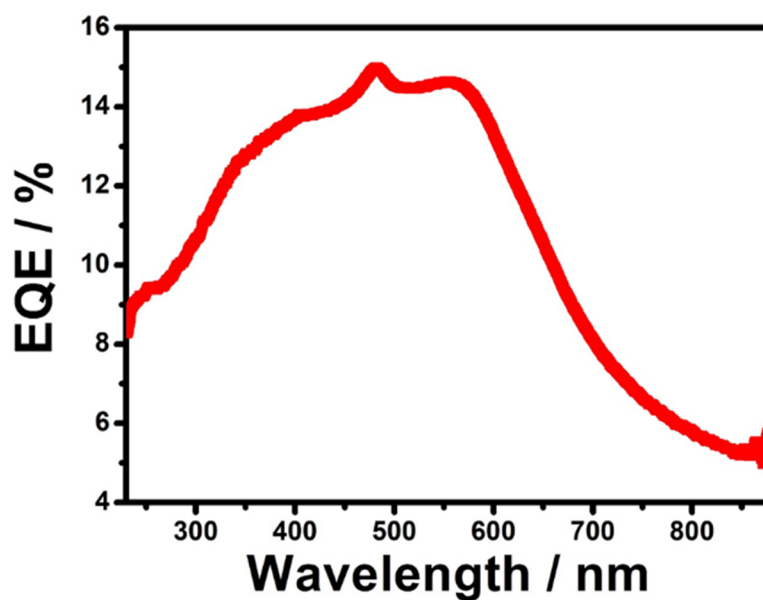


Figure S8. EQE result for the device with FTO/c-TiO₂/AgBiS₂/P3HT/Au structure.